

系所組別： 電機工程學系甲組

考試科目： 電子材料概論

考試日期： 0226，節次： 2

1. Explain the following noun. (20%)
 - a). Ionic Polarization
 - b). Dipolar Polarization
 - c). Atomic packing factor
 - d). Schottky Defect
 - e). Frenkel Defect
 - f). Gibbs Phase Rule
 - g). Seebeck Effect
 - h). Fermi-Dirac Statistics
 - i). Schottky Barrier Height
 - j). Ohmic contact
2. Copper (ion radius=0.125nm) and nickel (ion radius= 0.128nm) form a solid solution in all properties. Predict this result using the Hume-Rothery rules (15%)
3. Iron at 20°C is BCC with atoms of atomic radius 0.124nm. Calculate the lattice constant a for the cube edge of the iron unit cell (15%)
4. Draw the following crystallographic planes in cubic unit cell.(15%)
 - (a). (101) (b) ($\bar{1}\bar{1}0$) (c) (221)
 - (d) Draw a (110) plane in a BCC atomic-site unit cell, and list the position coordinates of the atoms whose centers are intersected by this plane.
5. Fig.(1) shows a hypothetical binary eutectic phase diagram on which we indicate an alloy of composition 0.27B. Calculate the following quantities (20%)
 - 甲、The fraction of primary solid that forms under equilibrium cooling at the eutectic temperature .
 - 乙、The fraction of liquid with the eutectic composition that will transform to two solid phases below the eutectic isotherm
 - 丙、The amount of α and β that will form from the liquid just below the eutectic isotherm.
 - 丁、The total amount of phase in the alloy at a temperature just below the eutectic temperature.
6. For intrinsic gallium arsenide, the room temperature electrical conductivity is $10^{-6} (\Omega\cdot\text{m})^{-1}$; the electron and hole mobilities are, respectively, 0.85 and $0.04 \text{ m}^2/\text{V}\cdot\text{s}$. Calculate the intrinsic carrier concentration n_i at room temperature. (15%)

(背面仍有題目,請繼續作答)

Fig.(1)

